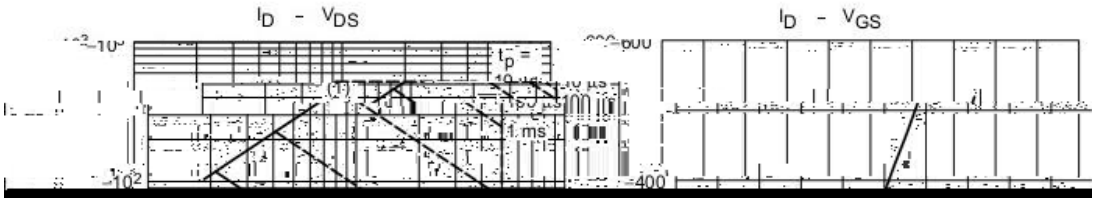
SOT-23 ṂṂ Ꝉ P ȣ ʃ, ѽ Ƶ ᒣ
P-CHANNEL MOSFET in a SOT-23 Plastic Package.

Ң Ầ ᵏ ɔ я ı F0 P RV ⁼ WWO ५ ɔ ت ì ì Æ ı Ầ ԋ ৯ ỷ ȏ ı گ ـ ɔ ΐ ד 4333Y ı ५ ᵀ DHF0T434 ‰ ˊ ᵡ ˡ ˎ ớ ļ ∂ ı ṇ ɾ β
Low threshold voltage, Direct interface to C-MOS, TTL etc, High-speed switching,ESD Improved

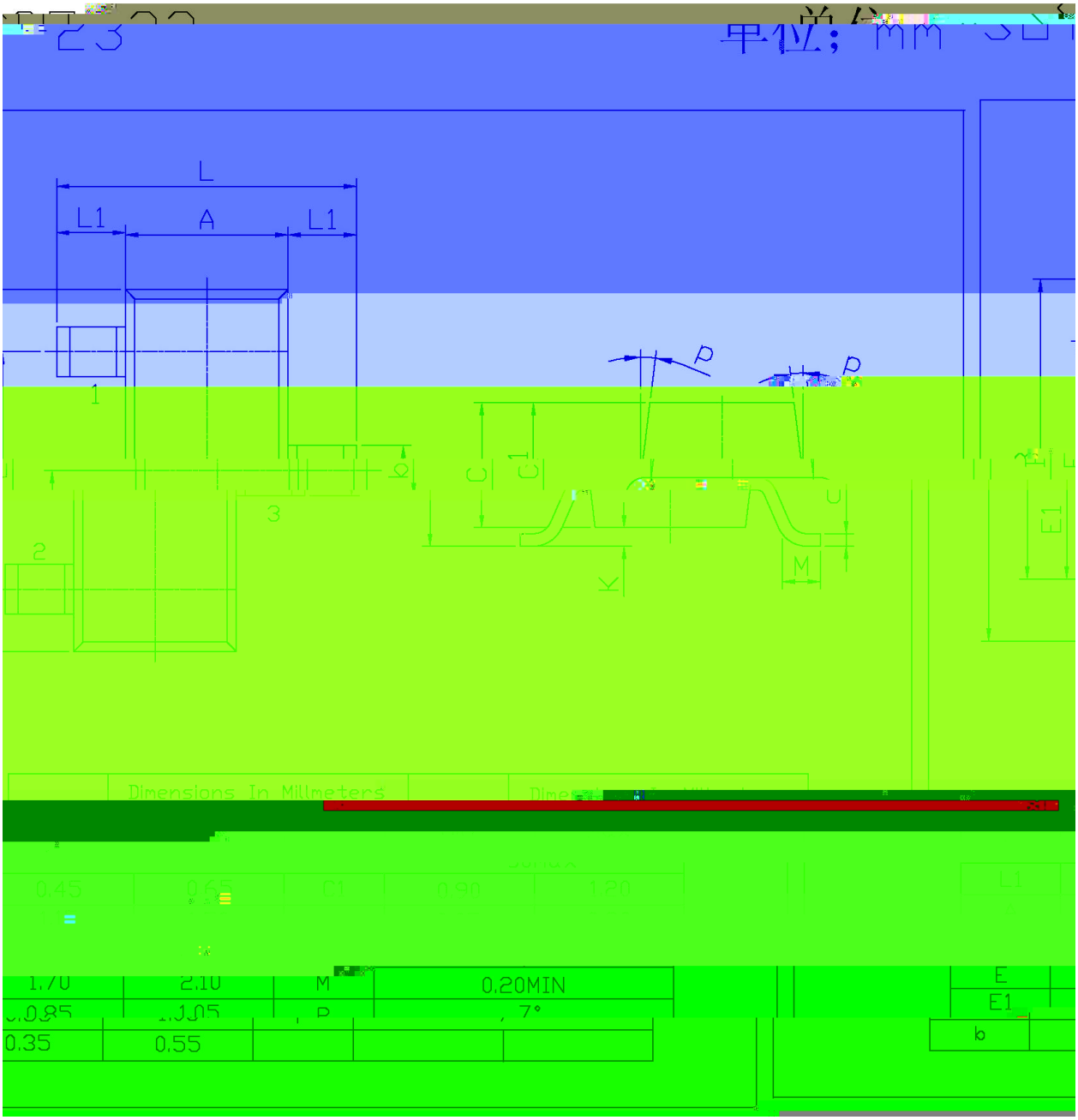
v ¨Ω Parameter	ϒ N Symbol	¨Ω Ö Rating	D Ч Unit
Drain-Source Voltage	V_{DSS}	-50	V
Drain Current – Continuous	I_D	-130	mA
Peak Drain Current	I_{DM}	-520	mA
Gate-Source Voltage	V_{GSS}	±20	V
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	500	/W
Storage Temperature Range	T_{stg}	-65 to 150	
Junction Temperature Range	T_j	150	

v ¨Ω Parameter	ϒ N Symbol	Ш :¦ ţ Test Conditions	ω ņ Ö Min	Ɛ ʒ Ö Typ	ω ² Ö Max	D Ч Unit
Drain–Source Breakdown Voltage	V_{DSS}	V_{GS}=0V I_D=-10μA	-50			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-0.8		-2.0	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V V_{DS}=-40V			-100	nA
		V_{GS}¥0V V_{DS}¥-50V			-10	μA 2D

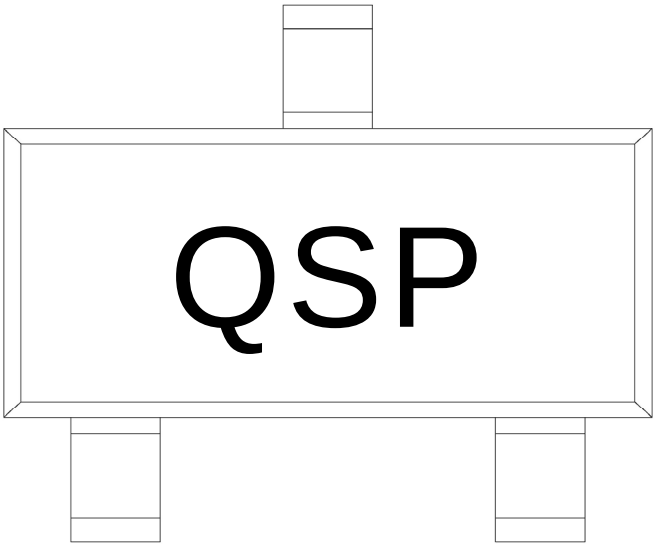
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



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SP χ ѭ ʒ ᴺ Γ

Note:

Q: Automobile halogen-free product Code

SP: Product Type.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

ب ˝ χ

1 Ĺ ♬ □ ỷ 150 Ḱ 200 ɬ ı `H ڑ 60 Ḱ 120sec;

2 Š Ө □ ỷ 255 ° 5 ɬ ı `H ڑ `Y ﾊ ㎞ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻩ ỷ ㎞ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:150~200 ɬ , Time:60~120sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3.Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp.:260 ° 5 ɬ Time:10 ° 1 sec

/ Packaging SPEC.

ɔ ` ﾔ Ł / REEL

Package Type